A B S T R A C T

A METHOD OF TREATING A WAFER SURFACE

The invention concerns a method of treating one or the other or both surfaces (12, 22) termed the "bonding" surfaces of a first wafer (10) termed the "donor" wafer and a second wafer (20) termed the "receiver" wafer intended to be bonded one against the other. The method is remarkable in that it comprises a cleaning and activation step carried out immediately prior to bonding said donor (10) and receiver (20) wafers, by applying to said bonding surface or surfaces (12, 22) a solution termed the "surface treatment" comprising at least about 97% of a solution of ammonia (NH_4OH) in water, preferably deionized, in a concentration by weight in the range from about 0.05% to 2%. The invention is applicable to fabricating structures used in the optics, electronics, or optoelectronics fields.

Translation of the title and the abstract as they were when originally filed by the Applicant. No account has been taken of any changes that may have been made subsequently by the PCT Authorities acting ex officio, e.g. under PCT Rules 37.2, 38.2, and/or 48.3.